

## EUROPEAN PATENT OFFICE

## Patent Abstracts of Japan

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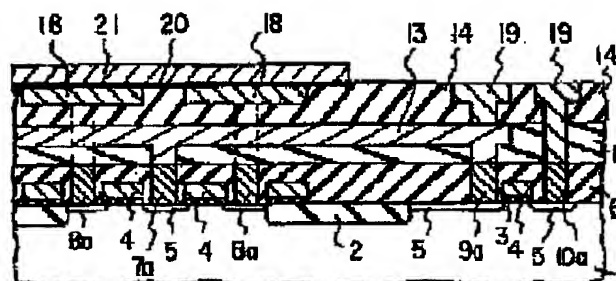
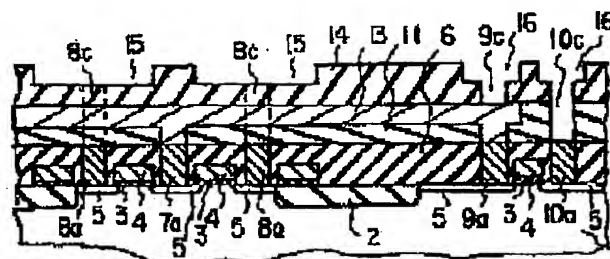
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TITLE : MANUFACTURE OF  
SEMICONDUCTOR MEMORY



**ABSTRACT :** **PROBLEM TO BE SOLVED:** To make it possible to facilitate the process of a storage electrode by forming an interlayer insulating film on an interconnection layer, depositing a conductive electrode material on the insulating film, processing conductive electrode material to simultaneously form the interconnection layers of the charge storage electrode of the cell and out of the cell region.

**SOLUTION:** The method for manufacturing a semiconductor memory comprises the steps of depositing an oxide film (14) as an interlayer insulating film, then opening the storage electrode connecting hole 8c of the cell and the connecting hole 9c of a peripheral circuit part by using lithographic method and etching technology, further forming a groove 15 for the storage electrode of the cell and the interconnection groove 16 of the peripheral circuit by using the lithographic method and the etching technology, then depositing the conductive electrode material, embedding the holes 8c, 9c, 10, the groove 15 for the electrode and the groove 16 for the circuit, and simultaneously forming the interconnection layer 19 of the electrode 18 and the circuit.

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